

# 60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE IntelliFET MOSFET

#### **Product Summary**

Continuous Drain Source Voltage: 60V

On-State Resistance: 500mΩ

Nominal Load Current (V<sub>IN</sub> = 5V): 1.3A

Clamping Energy: 90mJ

#### **Description**

The DIODES™ ZXMS6004FFQ is a self-protected low side IntelliFET™ MOSFET with logic level input. It integrates overtemperature, overcurrent, overvoltage (active clamp) and ESD protected logic level functionality. The ZXMS6004FFQ is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

#### **Applications**

- Especially suited for loads with a high in-rush current such as lamps and motors
- All types of resistive, inductive and capacitive loads in switching applications
- μC compatible power switch for 12V and 24V DC applications
- Automotive rated
- Replaces electromechanical relays and discrete circuits
- Linear mode capability the current-limiting protection circuitry is
  designed to de-activate at low V<sub>DS</sub> to minimize on state power
  dissipation. The maximum DC operating current is therefore
  determined by the thermal capability of the package/board
  combination, rather than by the protection circuitry. This does not
  compromise the product's ability to self-protect at low V<sub>DS</sub>.

#### **Features and Benefits**

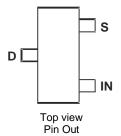
- Compact High Power Dissipation Package
- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Over Voltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Overcurrent Protection
- Input Protection (ESD)
- High Continuous Current Rating
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The ZXMS6004FFQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

#### **Mechanical Data**

- Package: SOT23F
- Package Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish@3
- Weight: 0.012 grams (Approximate)





### Ordering Information (Note 4)

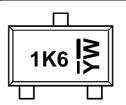
Part Number	Packago	Marking Reel Size (inches)		Tape Width (mm)	Pac	king
Fait Nulliber	er Package Marking		Reel Size (Illulies)	rape widin (ililii)	Qty.	Carrier
ZXMS6004FFQTA	SOT23F	1K6	7	12	3,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



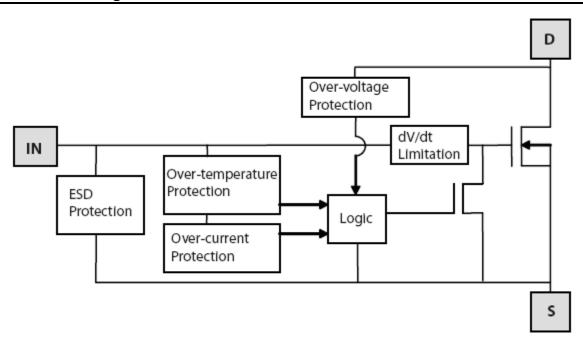
# **Marking Information**



1K6 = Product Type Marking Code Y or  $\overline{Y}$ : Year: 0 to 9 W or  $\overline{W}$ : Week: A to Z: 1 to 26 a to z: 27 to 52

z: Represents 52 & 53 Week

### **Functional Block Diagram**





# **Absolute Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Continuous Drain-Source Voltage	V <sub>D</sub> s	60	V
Drain-Source Voltage for Short Circuit Protection	V <sub>DS(SC)</sub>	36	V
Continuous Input Voltage	Vin	-0.5 +6	V
Continuous Input Current @-0.2V $\leq$ V <sub>IN</sub> $\leq$ 6V Continuous Input Current @V <sub>IN</sub> $<$ -0.2V or V <sub>IN</sub> $>$ 6V	I <sub>IN</sub>	No Limit   I <sub>IN</sub>   ≤2	mA
Pulsed Drain Current @VIN = 3.3V	I <sub>DM</sub>	2	Α
Pulsed Drain Current @VIN = 5V	Ірм	2.5	Α
Continuous Source Current (Body Diode)	Is	1	Α
Pulsed Source Current (Body Diode)	I <sub>SM</sub>	5	Α
Unclamped Single Pulse Inductive Energy, $T_J = +25^{\circ}C$ , $I_D = 0.5A$ , $V_{DD} = 24V$	Eas	90	mJ
Electrostatic Discharge (Human Body Model)	V <sub>ESD</sub>	4,000	V
Charged Device Model	Vcdм	1,000	V

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation @T <sub>A</sub> = +25°C (Note 5)	Pp	0.83	W
Linear Derating Factor		6.66	mW/°C
Power Dissipation @T <sub>A</sub> = +25°C (Note 6)	Pp	1.5	W
Linear Derating Factor	i B	12.0	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	Reja	150	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	83	°C/W
Thermal Resistance, Junction to Case (Note 7)	Rejc	44	°C/W
Operating Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C

# **Recommended Operating Conditions**

The ZXMS6004FFQ is optimized for use with µC operating from 3.3V and 5V supplies.

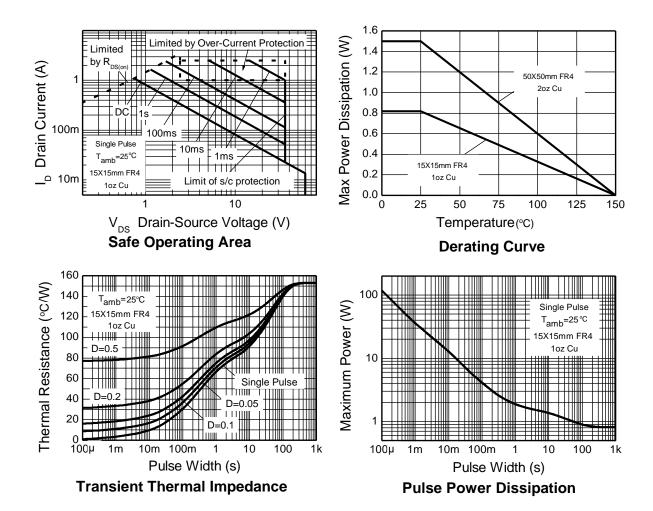
Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	Vin	0	5.5	V
Ambient Temperature Range	TA	-40	+125	°C
High Level Input Voltage for MOSFET to be On	ViH	3	5.5	V
Low Level Input Voltage for MOSFET to be Off	V <sub>IL</sub>	0	0.7	V
Peripheral Supply Voltage (Voltage to Which Load is Referred)	VP	0	36	V

Notes:

- 5. For a device surface mounted on 15mm x 15mm single sided, 1oz weight copper on 1.6mm FR4 board, in still air conditions.
  6. For a device surface mounted on 50mm x 50mm single sided, 2oz weight copper on 1.6mm FR4 board, in still air conditions.
  7. Thermal resistance from junction and the mounting surfaces of the drain pins.



# **Typical Thermal Characteristics**





# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

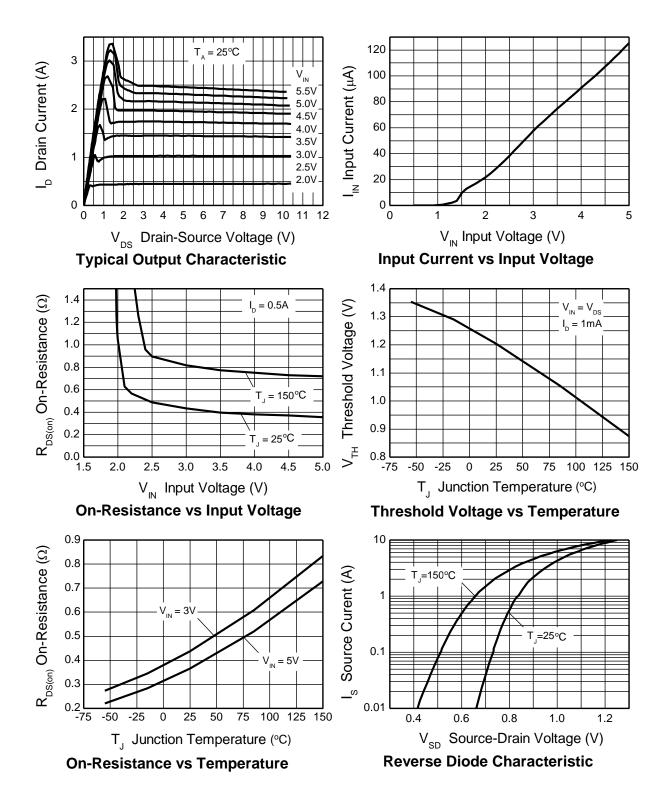
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics						
Drain-Source Clamp Voltage	V <sub>DS(AZ)</sub>	60	65	70	V	I <sub>D</sub> = 10mA
Off-State Drain Current	IDSS	_	_	500	nA	V <sub>DS</sub> = 12V, V <sub>IN</sub> = 0V
Off-State Drain Current		_	_	1	μΑ	V <sub>DS</sub> = 36V, V <sub>IN</sub> = 0V
Input Threshold Voltage	VIN(TH)	0.7	1	1.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA
Input Current	Luci	_	60	100	μΑ	$V_{IN} = +3V$
Input Current	lın	_	120	200		$V_{IN} = +5V$
Input Current while Overtemperature Active	_	_	_	220	μΑ	V <sub>IN</sub> = +5V
Static Drain-Source On-State Resistance	D	_	400	600	mΩ	$V_{IN} = +3V, I_D = 0.5A$
Static Drain-Source On-State Resistance	RDS(ON)		350	500	11122	$V_{IN} = +5V, I_D = 0.5A$
Continuous Drain Current (Note 5)	- ID	0.9	_	_		V <sub>IN</sub> = 3V, T <sub>A</sub> = +25°C
Continuous Drain Current (Note 5)		1.0	_	_	Α	V <sub>IN</sub> = 5V, T <sub>A</sub> = +25°C
Continuous Dunin Commant (Nata C)		1.2	_	_		$V_{IN} = 3V, T_A = +25^{\circ}C$
Continuous Drain Current (Note 6)		1.3	_	_		$V_{IN} = 5V, T_A = +25^{\circ}C$
Current Limit (Note 9)	I <sub>D(LIM)</sub>	0.7	1.7	_	Α	V <sub>IN</sub> = +3V
Current Limit (Note 8)		1	2.2	_		$V_{IN} = +5V$
Dynamic Characteristics						•
Turn-On Delay Time	t <sub>D</sub> (ON)	-	5	_		
Rise Time	t <sub>R</sub>	_	10	_		\\ 40\\ I= 0.5A \\ 5\\
Turn-Off Delay Time	tD(OFF)	_	45	_	μs	V <sub>DD</sub> = 12V, I <sub>D</sub> = 0.5A, V <sub>GS</sub> = 5V
Fall Time	fF	_	15	_		
Overtemperature Protection						
Thermal Overload Trip Temperature (Note 9)	TJT	+150	+175	_	°C	
Thermal Hysteresis (Note 9)			+10		°C	_

Notes:

- 5. For a device surface mounted on 15mm x 15mm single sided, 1oz weight copper on 1.6mm FR4 board, in still air conditions. 6. For a device surface mounted on 50mm x 50mm single sided, 2oz weight copper on 1.6mm FR4 board, in still air conditions.
- 7. Thermal resistance from junction and the mounting surfaces of the drain pins.
- 8. The drain current is restricted only when the device is in saturation (see graph 'Typical Output Characteristic'). This allows the device to be used in the fully on-state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.
- 9. Overtemperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods.

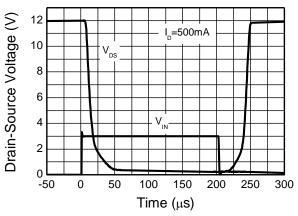


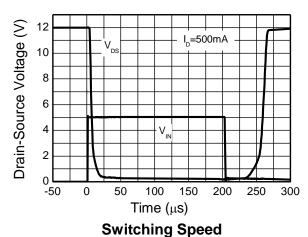
#### **Typical Performance Characteristics**





# **Typical Performance Characteristics** (continued)





### **Switching Speed**

2.5  $V_{IN} = 5V$ I<sub>D</sub> Drain Current (A)  $V_{DS} = 15V$ 2.0  $R_D = 0\Omega$ 1.5 1.0 0.5 0.0 0 5 10 15 20 Time (ms)

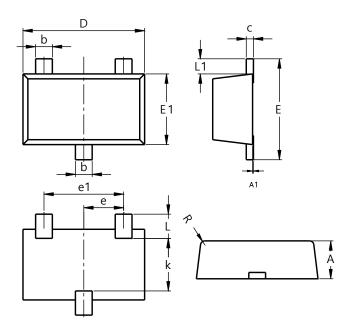
**Typical Short Circuit Protection** 



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23F

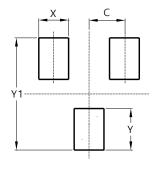


SOT23F						
Dim	Min Max Typ					
Α	0.80	1.00	0.90			
A1	0.00	0.10	0.01			
b	0.35	0.50	0.44			
C	0.10	0.20	0.16			
D	2.80	3.00	2.90			
е	0.95 REF					
e1	1.90 REF					
Е	2.30	2.50	2.40			
E1	1.50	1.70	1.65			
k	1.20	-	-			
Г	0.30	0.65	0.50			
L1	0.30	0.50	0.40			
R	0.05	0.15	-			
All Dimensions in mm						

# **Suggested Pad Layout**

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html for the latest version.$ 

#### SOT23F



Dimensions	Value (in mm)		
С	0.95		
Х	0.80		
Y	1.110		
Y1	3.000		



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